

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

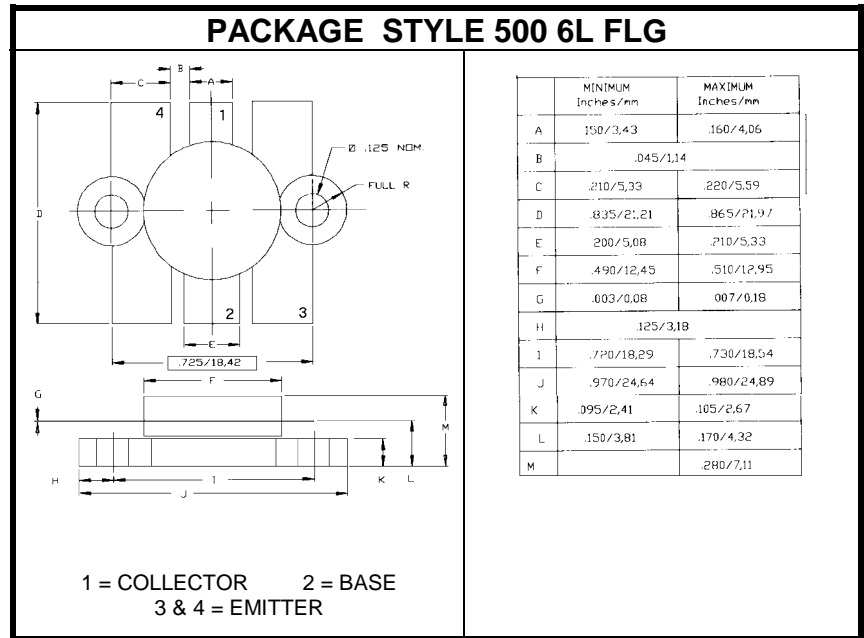
The **ASI TPV385** is Designed for Operation in Band III TV Transposers and Transmitter Amplifiers from 170 to 230 MHz.

FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballast Resistors
- Internal Input Matching
- Common Emitter

MAXIMUM RATINGS

I_C	10 A (CONT)
V_{CB}	65 V
V_{CE}	35 V
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.5 °C/W


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA			35			V
BV_{CER}	I _C = 50 mA	R _{BE} = 10 Ω		60			V
BV_{CBO}	I _C = 50 mA			65			V
BV_{EBO}	I _E = 10 mA			4.0			V
h_{FE}	V _{CE} = 5.0 V	I _C = 1.0 A		20		100	---
C_{ob}	V _{CB} = 30 V	f = 1.0 MHz			65	85	pF
G_P IMD₁	V _{CE} = 28 V	P _{out} = 14 W	f = 225 MHz	14	15	-53	dB dB
ψ	V _{CE} = 28 V P _{out} = 14 W	ALL PHASE ANGLES LOAD VSWR = ∞:1		NO DEGRADATION IN OUTPUT POWER			